



April 2000

QFET™

FQB7N80 / FQI7N80

800V N-Channel MOSFET

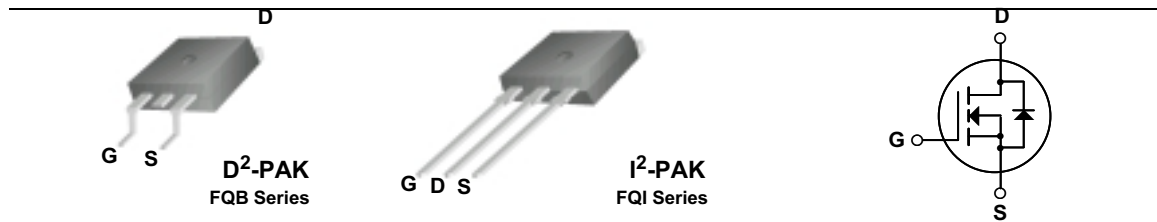
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply.

Features

- 6.6A, 800V, $R_{DS(on)} = 1.5\Omega @ V_{GS} = 10V$
- Low gate charge (typical 40 nC)
- Low Crss (typical 19 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQB7N80 / FQI7N80	Units
V _{DSS}	Drain-Source Voltage	800	V
I _D	Drain Current - Continuous (T _C = 25°C)	6.6	A
	- Continuous (T _C = 100°C)	4.2	A
I _{DM}	Drain Current - Pulsed (Note 1)	26.4	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	580	mJ
I _{AR}	Avalanche Current (Note 1)	6.6	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	16.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *	3.13	W
	Power Dissipation (T _C = 25°C)	167	W
	- Derate above 25°C	1.34	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	0.75	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient *	--	40	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	800	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.77	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800 V, V _{GS} = 0 V	--	--	10	μA
		V _{DS} = 640 V, T _C = 125°C	--	--	100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.3 A	--	1.2	1.5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 3.3 A (Note 4)	--	5	--	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1420	1850	pF
C _{oss}	Output Capacitance		--	150	195	pF
C _{rss}	Reverse Transfer Capacitance		--	19	25	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 6.6 A, R _G = 25 Ω (Note 4, 5)	--	35	80	ns
t _r	Turn-On Rise Time		--	80	170	ns
t _{d(off)}	Turn-Off Delay Time		--	95	200	ns
t _f	Turn-Off Fall Time		--	55	120	ns
Q _g	Total Gate Charge	V _{DS} = 640 V, I _D = 6.6 A, V _{GS} = 10 V (Note 4, 5)	--	40	52	nC
Q _{gs}	Gate-Source Charge		--	8.5	--	nC
Q _{gd}	Gate-Drain Charge		--	20	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	6.6	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	26.4	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 6.6 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 6.6 A, di _F / dt = 100 A/μs (Note 4)	--	400	--	ns
Q _{rr}	Reverse Recovery Charge		--	4.3	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 25mH, I_{AS} = 6.6A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 6.6A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

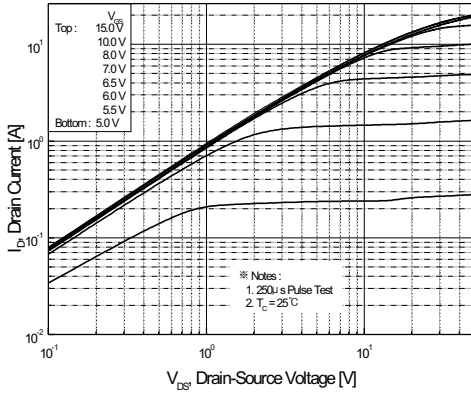


Figure 1. On-Region Characteristics

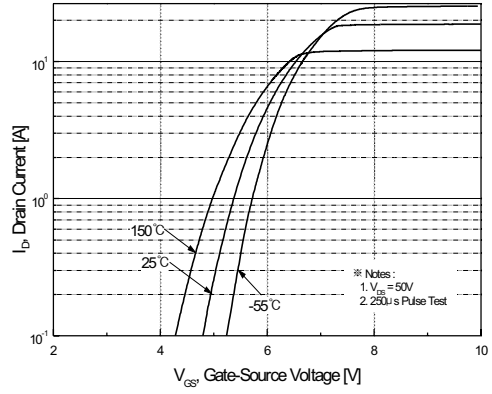


Figure 2. Transfer Characteristics

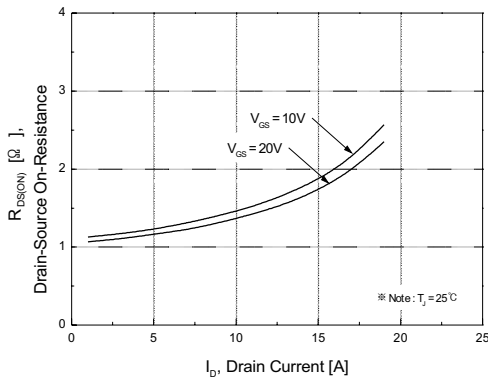


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

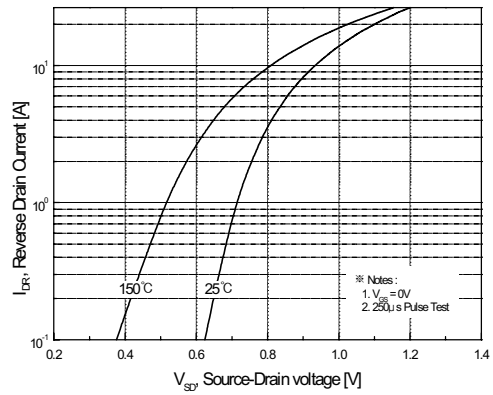


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

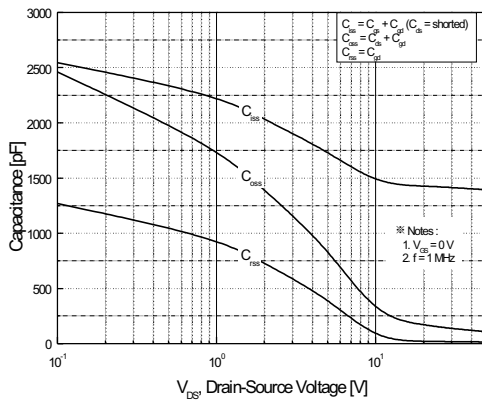


Figure 5. Capacitance Characteristics

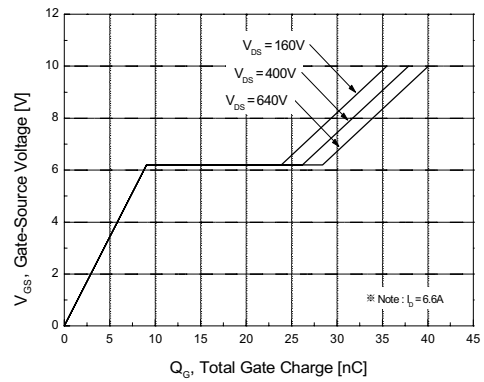


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

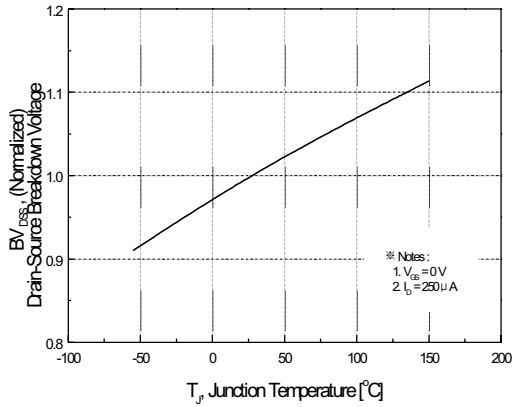


Figure 7. Breakdown Voltage Variation vs. Temperature

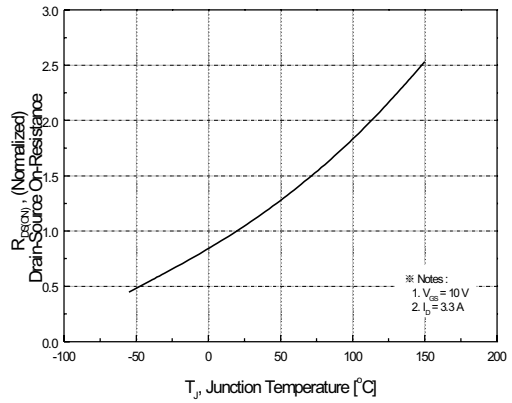


Figure 8. On-Resistance Variation vs. Temperature

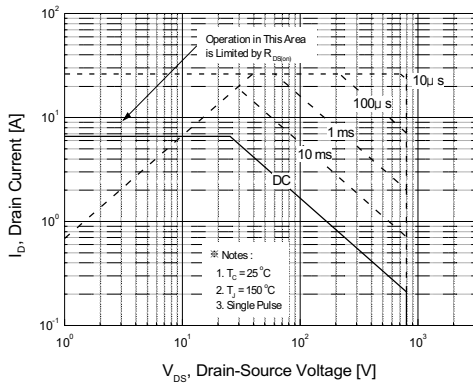


Figure 9. Maximum Safe Operating Area

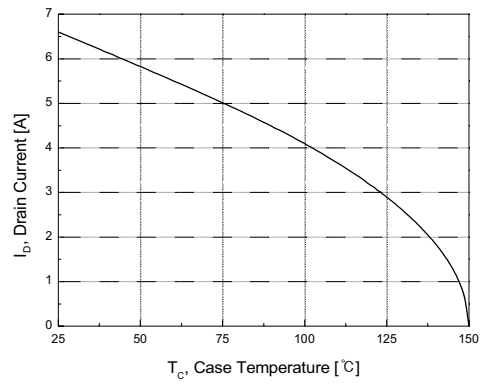


Figure 10. Maximum Drain Current vs. Case Temperature

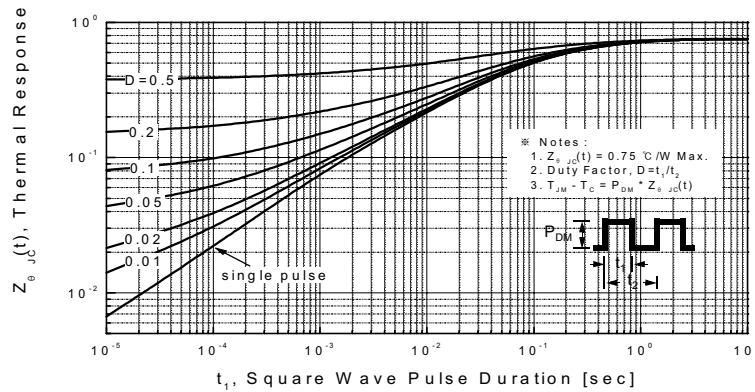


Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

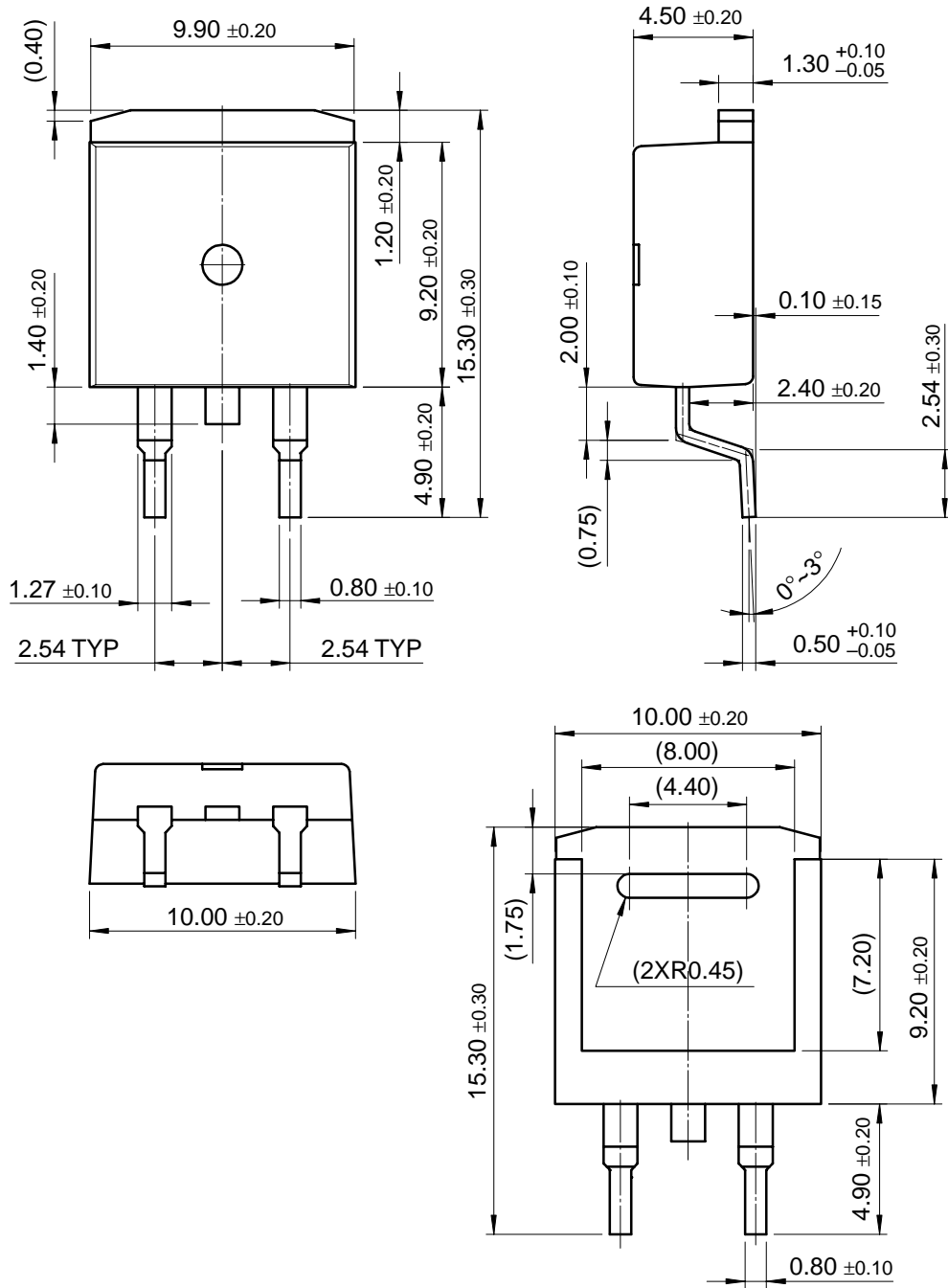


Peak Diode Recovery dv/dt Test Circuit & Waveforms



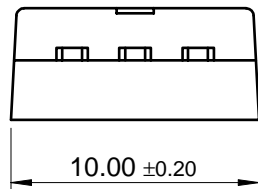
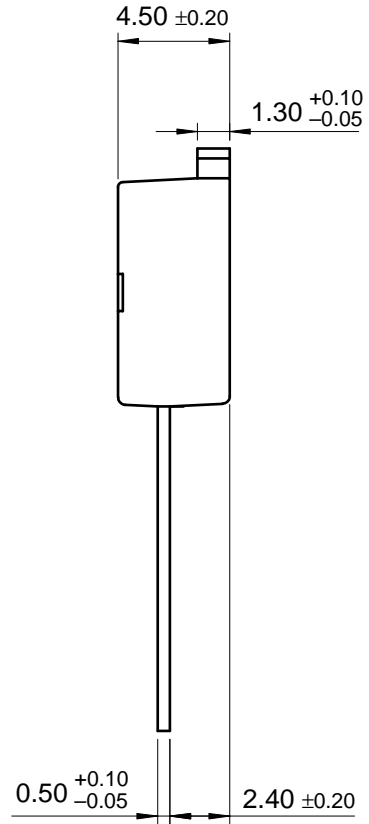
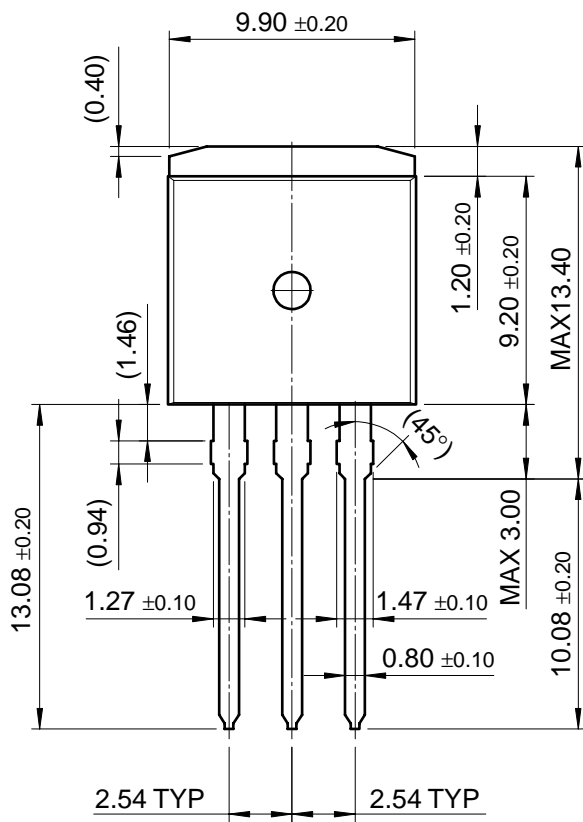
Package Dimensions

D²PAK



Package Dimensions (Continued)

I²PAK



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